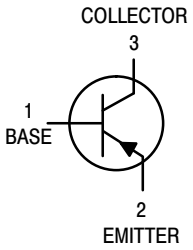
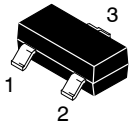
General Purpose Transistors

PNP Silicon

BC807-16L, BC807-25L, BC807-40L





SOT−23
CASE 318
STYLE 6

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector − Emitter Voltage	V_{CEO}	−45	V
Collector − Base Voltage	V_{CBO}	−50	V
Emitter − Base Voltage	V_{EBO}	−5.0	V
Collector Current − Continuous	I_C	−500	mAdc

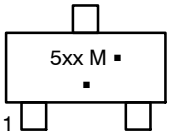
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR− 5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 1)	$R_{\theta JA}$	436	°C/W
Total Device Dissipation Alumina Substrate, (Note 1) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient (Note 2)	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR−4 Board, 1 oz. Cu, 100mm^2.
2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.

MARKING DIAGRAM



5xx = Device Code
xx = A1, B1, or C
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

© Semiconductor Components Industries, LLC, 1997

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector − Emitter Breakdown Voltage (I_C = −10 mA)		$V_{(BR)CEO}$	−45	−	−	V
Collector − Emitter Breakdown Voltage (V_{EB} = 0, I_C = −10 μA)		$V_{(BR)CES}$	−50	−	−	V
Emitter − Base Breakdown Voltage (I_E = −1.0 μA)		$V_{(BR)EBO}$	−5.0	−	−	V
Collector Cutoff Current		I_{CBO}				
(V_{CB} = −20 V)			−	−	−100	nA
(V_{CB} = −20 V, T_J = 150°C)			−	−	−5.0	μA
ON CHARACTERISTICS						
DC Current Gain		h_{FE}				−
(I_C = −100 mA, V_{CE} = −1.0 V)	BC807−16, SBC80−16L		100	−	250	
	BC807−25, SBC807−25L		160	−	400	
	BC807−40, SBC807−40L		250	−	600	
(I_C = −500 mA, V_{CE} = −1.0 V)			40	−	−	
Collector − Emitter Saturation Voltage (I_C = −500 mA, I_B = −50 mA)		$V_{CE(sat)}$	−	−	−0.7	V
Base − Emitter On Voltage (I_C = −500 mA, V_{CE} = −1.0 V)		$V_{BE(on)}$	−	−	−1.2	V
SMALL−SIGNAL CHARACTERISTICS						
Current − Gain − Bandwidth Product (I_C = −10 mA, V_{CE} = −5.0 Vdc, f = 100 MHz)		f_T	100	−	−	MHz
Output Capacitance (V_{CB} = −10 V, f = 1.0 MHz)		C_{obo}	−	10	−	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Device	Specific Marking	Package	Shipping†
BC807−16LT1G	5A1	SOT−23 (Pb−Free)	3000 / Tape & Reel
SBC807−16LT1G*			
BC807−16LT3G	5A1		10,000 / Tape & Reel
SBC807−16LT3G*			
BC807−25LT1G	5B1		3000 / Tape & Reel
SBC807−25LT1G*			
BC807−25LT3G	5B1		10,000 / Tape & Reel
SBC807−25LT3G*			
BC807−40LT1G	5C		3000 / Tape & Reel
SBC807−40LT1G*			
BC807−40LT3G	5C		10,000 / Tape & Reel
SBC807−40LT3G*			

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

TYPICAL CHARACTERISTICS − BC807−16LT1

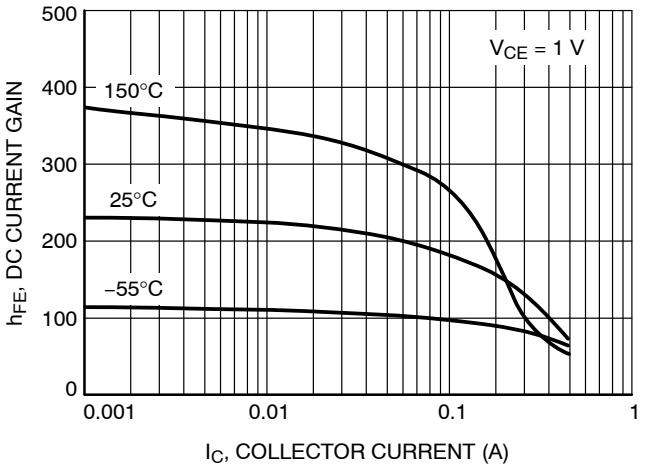


Figure 1. DC Current Gain vs. Collector Current

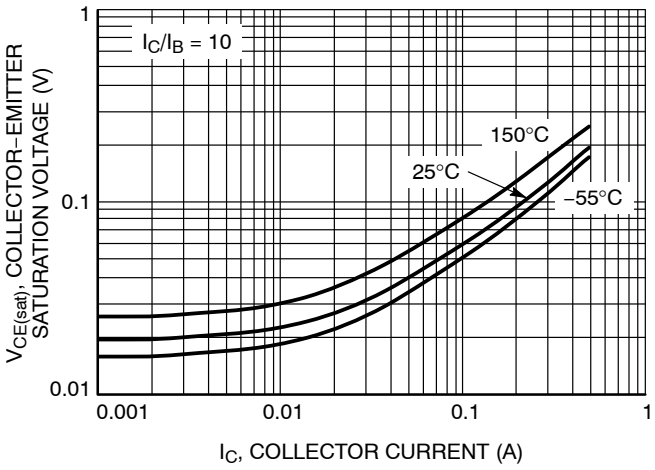


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

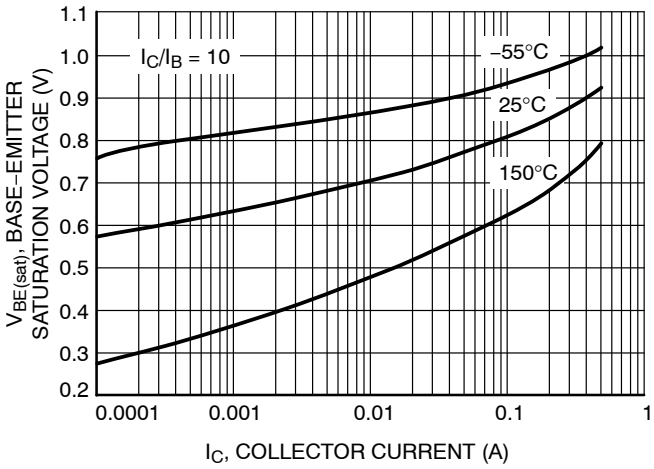


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

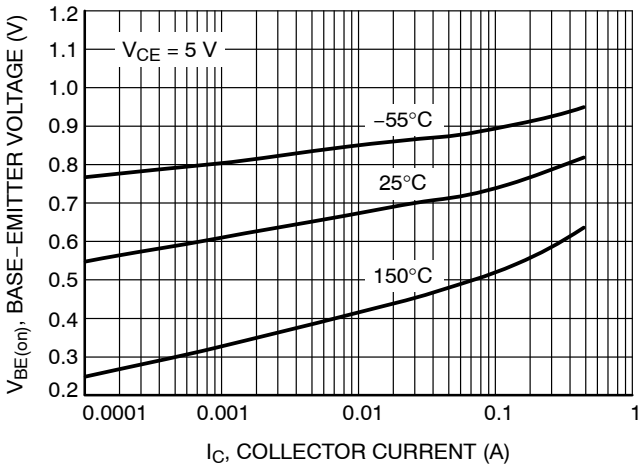


Figure 4. Base Emitter Voltage vs. Collector Current

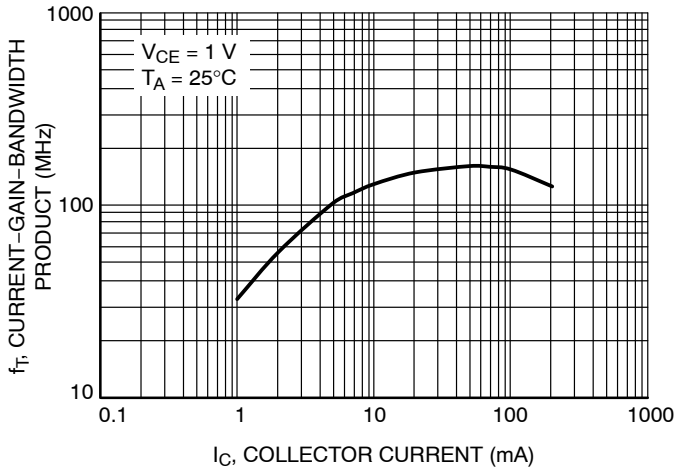


Figure 5. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS − BC807−16LT1

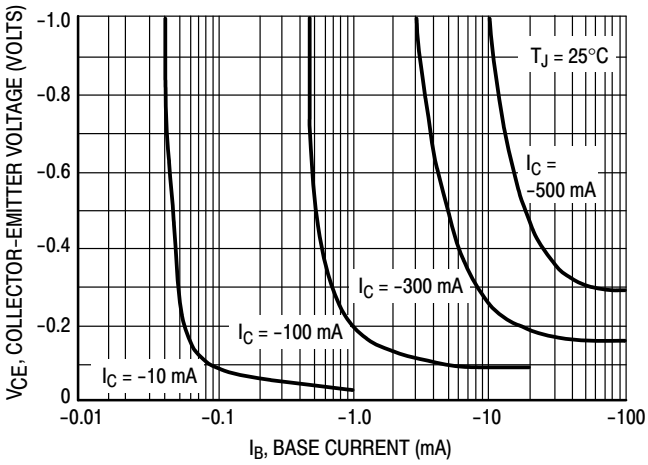


Figure 6. Saturation Region

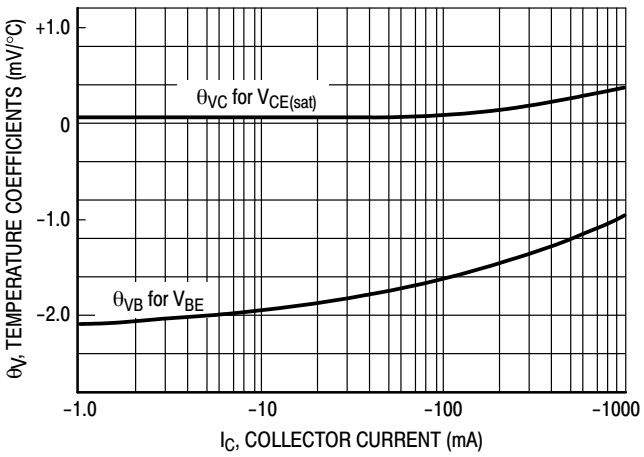


Figure 7. Temperature Coefficients

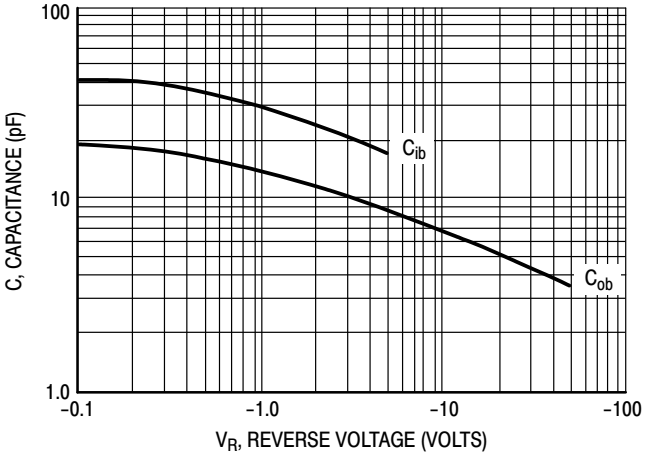


Figure 8. Capacitances

TYPICAL CHARACTERISTICS − BC807−25LT1

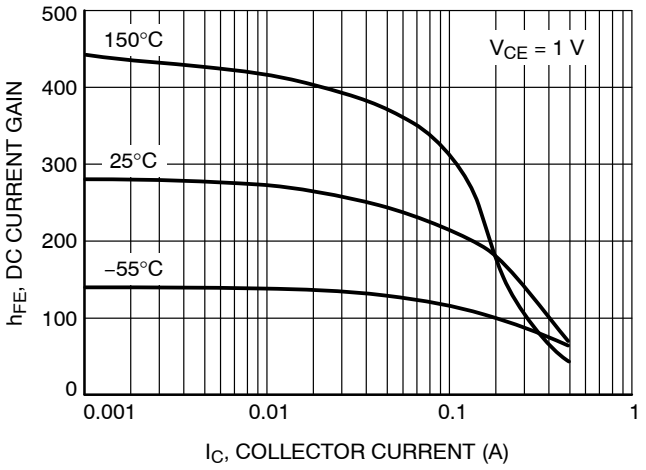


Figure 9. DC Current Gain vs. Collector Current

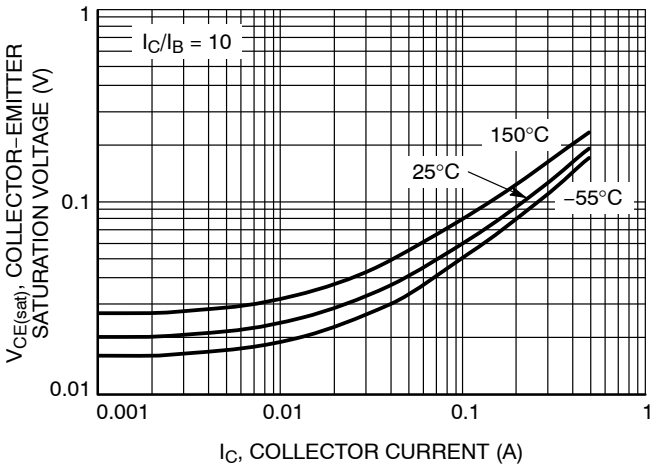


Figure 10. Collector Emitter Saturation Voltage vs. Collector Current

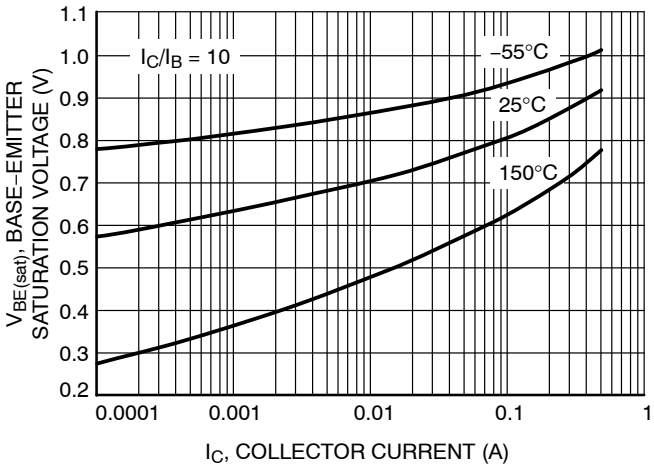


Figure 11. Base Emitter Saturation Voltage vs. Collector Current

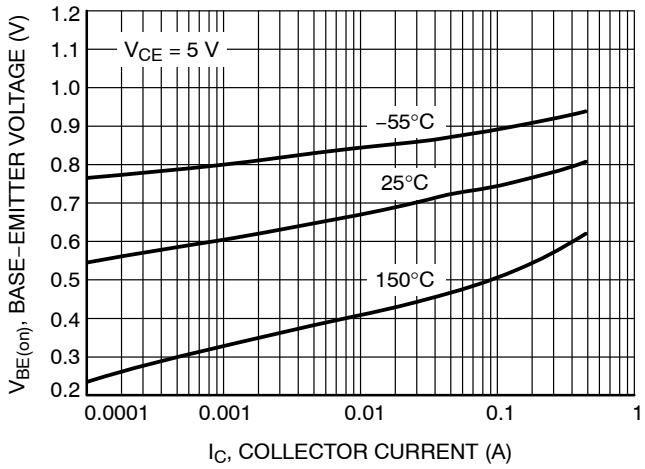


Figure 12. Base Emitter Voltage vs. Collector Current

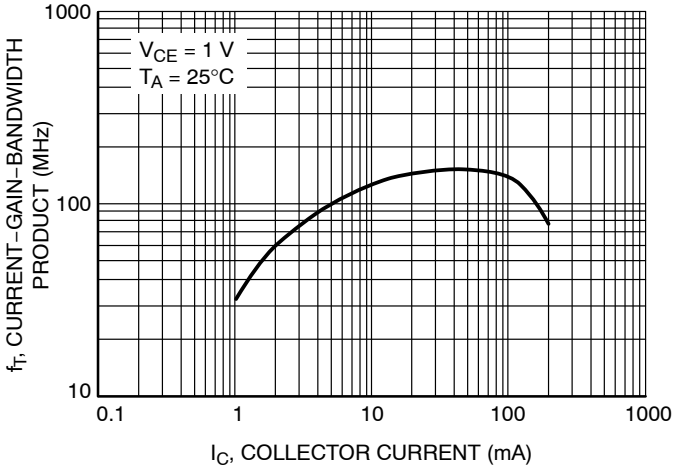


Figure 13. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS − BC807−25LT1

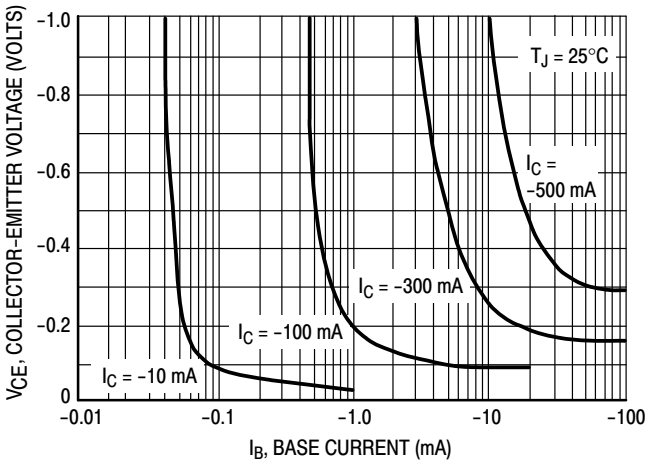


Figure 14. Saturation Region

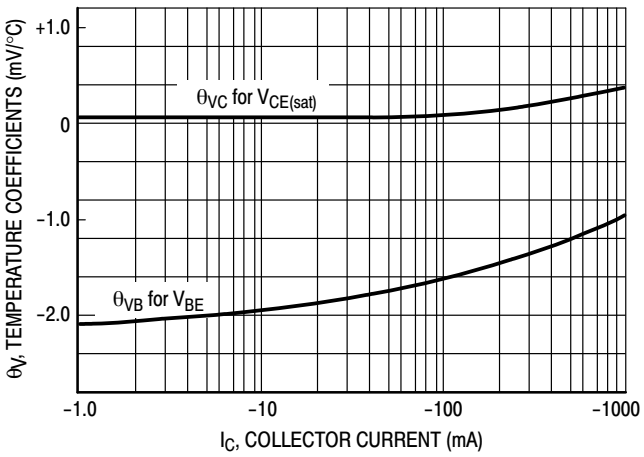


Figure 15. Temperature Coefficients

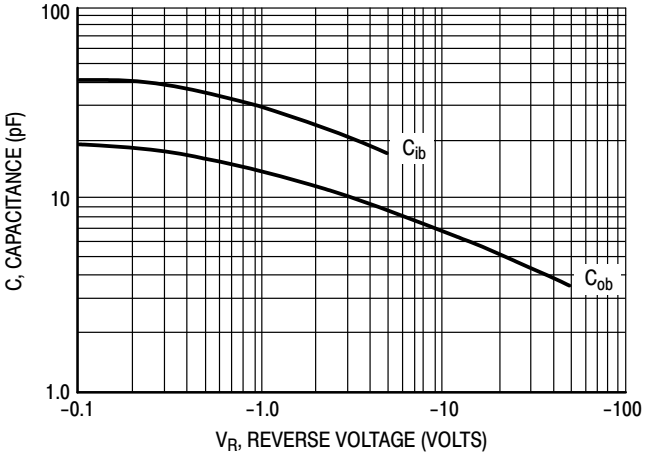


Figure 16. Capacitances

TYPICAL CHARACTERISTICS − BC807−40LT1

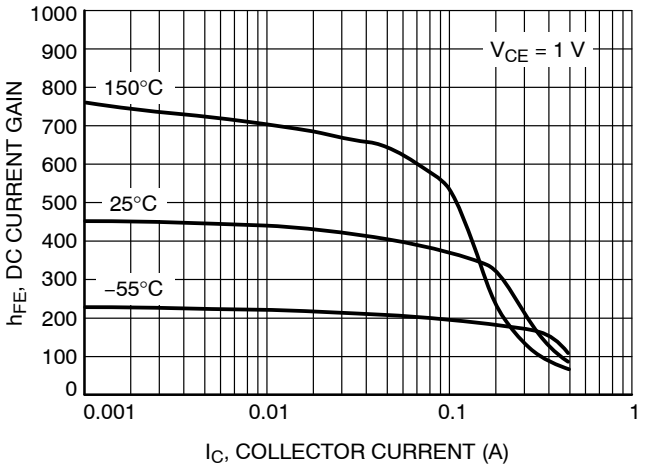


Figure 17. DC Current Gain vs. Collector Current

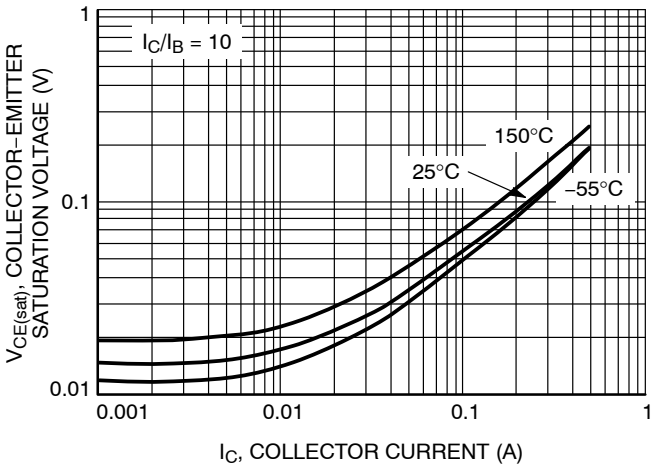


Figure 18. Collector Emitter Saturation Voltage vs. Collector Current

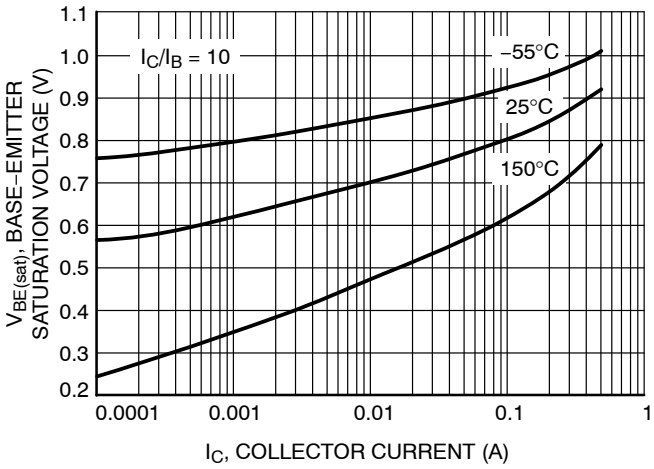


Figure 19. Base Emitter Saturation Voltage vs. Collector Current

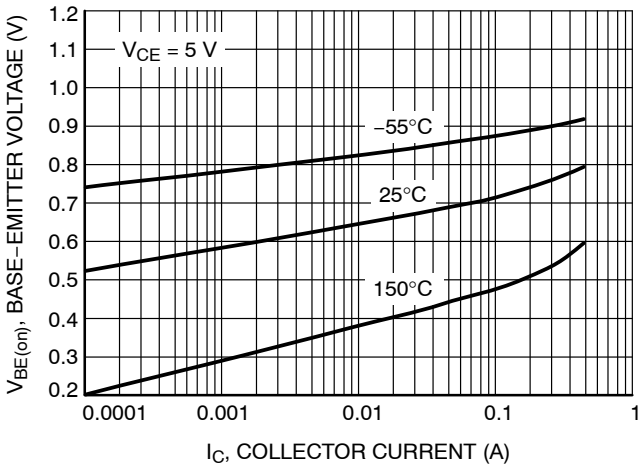


Figure 20. Base Emitter Voltage vs. Collector Current

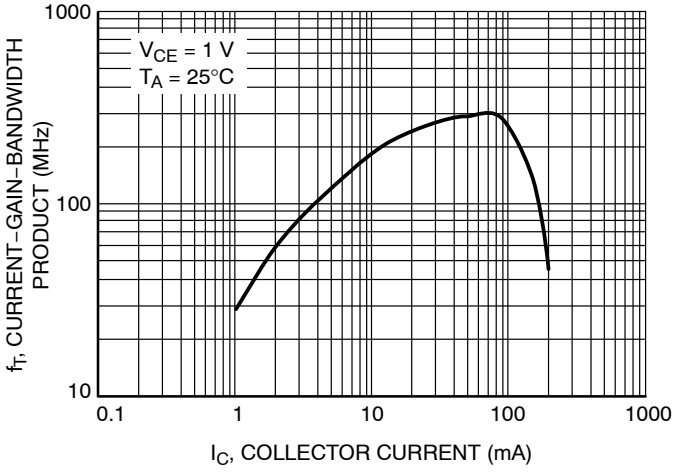


Figure 21. Current Gain Bandwidth Product vs. Collector Current

TYPICAL CHARACTERISTICS − BC807−40LT1

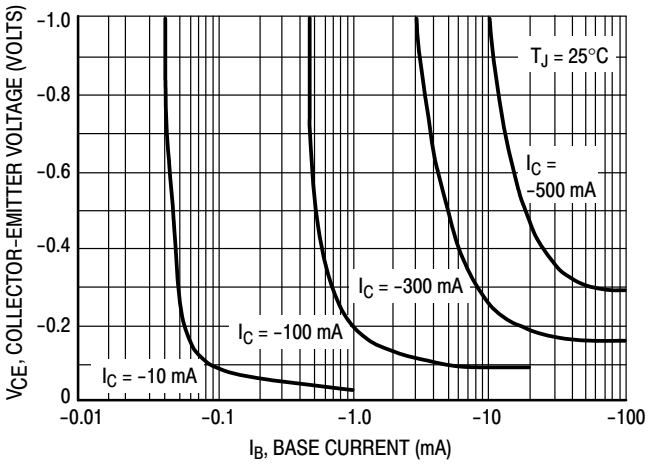


Figure 22. Saturation Region

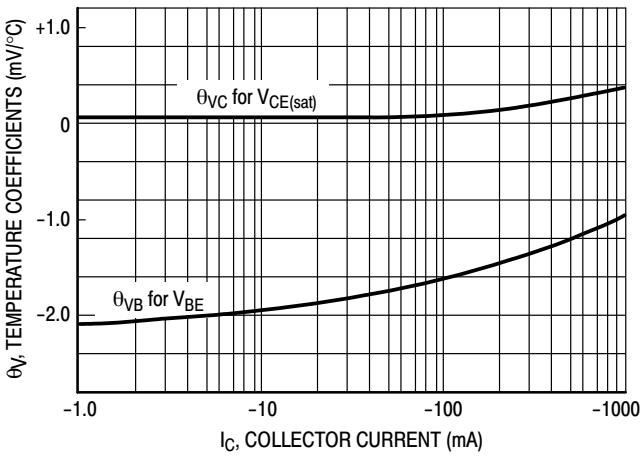


Figure 23. Temperature Coefficients

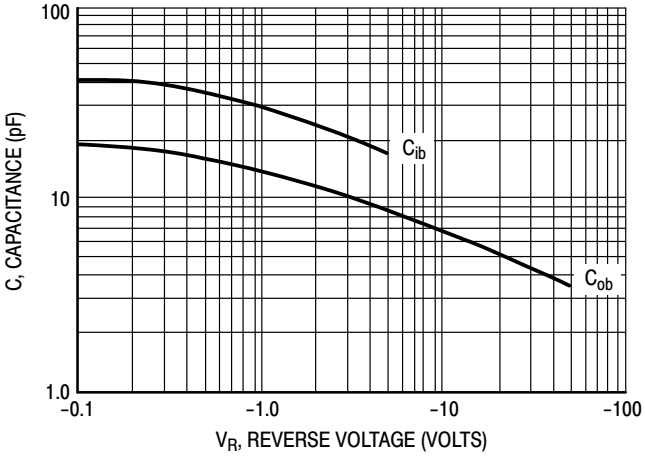


Figure 24. Capacitances

TYPICAL CHARACTERISTICS − BC807−16LT1, BC807−25LT1, BC807−40LT1

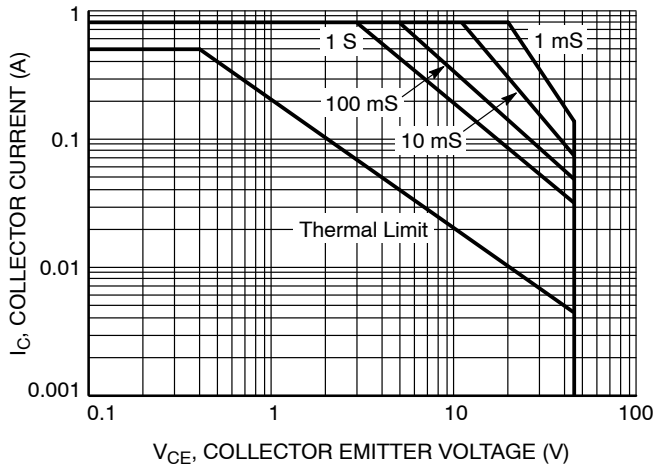
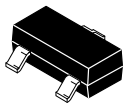


Figure 25. Safe Operating Area

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

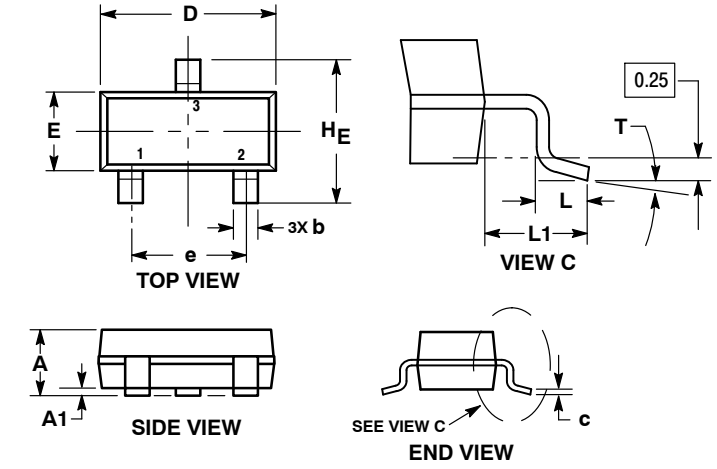
ON Semiconductor®



SOT−23 (TO−236)
CASE 318−08
ISSUE AS

DATE 30 JAN 2018

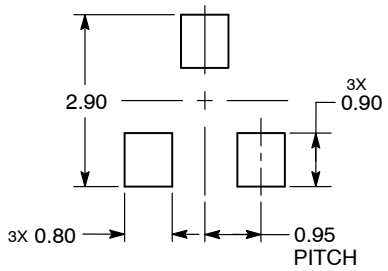
SCALE 4:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

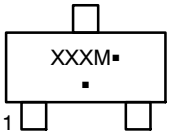
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	−−−	10°	0°	−−−	10°

RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	SOT−23 (TO−236)	PAGE 1 OF 1

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

onsemi, ONSEMI , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT
North American Technical Support:
Voice Mail: 1 800−282−9855 Toll Free USA/Canada
Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:
Phone: 00421 33 790 2910
For additional information, please contact your local Sales Representative

◊